

Product Overview

NGTB30N60IHLWG: IGBT, Field Stop (FS), 30 A, 600 V

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for half bridge resonant applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using Trench with Fieldstop Technology
- Low Switching Loss

Applications

- Half Bridge IH

Benefits

- Low Conduction Loss
- Reduces System Power Dissipation

End Products

- Inductive Heating Hobs

For more information please contact your local sales support at www.onsemi.com.

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